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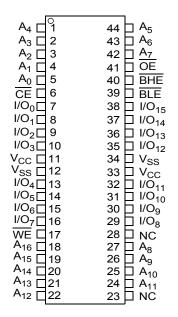


Product Portfolio

Power Diss			ssipation	on							
Product Porms V _{CC} Range (V) Spe		Speed	Operating I _{CC} (mA)				Standby L (A)				
Product	Range				(ns)	f = 1MHz		f = f _{max}		—Standby I _{SB2} (μΑ)	
		Min	Typ [1]	Max		Typ [1]	Max	Typ [1]	Max	Typ [1]	Max
CY62137FV30LL	Automotive-A	2.2 V	3.0 V	3.6 V	45	1.6	2.5	13	18	1	5
	Automotive-E	2.2 V	3.0 V	3.6 V	55	2	3	15	25	1	20

Pin Configuration

Figure 1. 44-pin TSOP II pinout [2]



Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC(typ)}, T_A = 25 °C.
 NC pins are not connected on the die.



Maximum Ratings

Exceeding the maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage temperature-65 °C to + 150 °C Ambient temperature with power applied-55 °C to + 125 °C Supply voltage to ground potential-0.3 V to 3.9 V DC voltage applied to outputs in High Z state $^{[3,\ 4]}$ -0.3 V to 3.9 V

DC input voltage [4]	0.3 V to 3.9 V
Output current into outputs (LOW)	20 mA
Static discharge voltage (MIL-STD-883, method 3015)	> 2001 V
Latch up current	> 200 mA

Operating Range

Device	Range	Ambient Temperature	V cc ^[5]
CY62137FV30LL	Automotive-A	–40 °C to +85 °C	
	Automotive-E	–40 °C to +125 °C	3.6 V

Electrical Characteristics

Over the Operating Range

D	Dan and a thoro	Test Conditions		45 ns (Automotive-A)			55 ns (Automotive-E)			11:4
Parameter	Description			Min	Typ [6]	Max	Min	Typ [6]	Max	Unit
V _{OH}	Output high voltage	$2.2 \le V_{CC} \le 2.7$	$I_{OH} = -0.1 \text{ mA}$	2.0	_	_	2.0	_	-	V
		$2.7 \le V_{CC} \le 3.6$	$I_{OH} = -1.0 \text{ mA}$	2.4	_	_	2.4	_	_	V
V _{OL}	Output low voltage	2.2 ≤ V _{CC} ≤ 2.7	$I_{OL} = 0.1 \text{ mA}$	-	_	0.4	-	_	0.4	V
		$2.7 \le V_{CC} \le 3.6$	I _{OL} = 2.1 mA	-	_	0.4	-	_	0.4	V
V_{IH}	Input high voltage	$2.2 \le V_{CC} \le 2.7$		1.8	_	$V_{CC} + 0.3$	1.8	_	$V_{CC} + 0.3$	V
		$2.7 \le V_{CC} \le 3.6$		2.2	_	$V_{CC} + 0.3$	2.2	_	$V_{CC} + 0.3$	V
V_{IL}	Input low voltage	$2.2 \le V_{CC} \le 2.7$		-0.3	_	0.6	-0.3	_	0.6	V
		2.7 ≤ V _{CC} ≤ 3.6		-0.3	_	0.8	-0.3	_	0.8	V
I _{IX}	Input leakage current	$GND \leq V_I \leq V_CC$		-1	_	+1	-4	_	+4	μΑ
I _{OZ}	Output leakage current	$GND \leq V_O \leq V_{CC}$	Output disabled	-1	_	+1	-4	_	+4	μΑ
I _{CC}	V _{CC} operating supply	$f = f_{max} = 1/t_{RC}$	$V_{CC} = V_{CC(max)}$	_	13	18	_	15	25	mA
	current	f = 1 MHz	I _{OUT} = 0 mA CMOS levels	_	1.6	2.5	_	2	3	
I _{SB1} ^[7]	Automatic power down current – CMOS inputs	$\frac{\overline{CE} > V_{CC} - 0.2 V_{IN} \geq V_{CC} - 0.2 V_{IN} \geq V_{CC} - 0.2 V_{IN} \geq V_{CC} - 0.2 V_{CC} = $	≥ V _{CC} – 0.2 V, V, V _{IN} ≤ 0.2 V, _and data only),	_	1	5	-	1	20	μΑ
I _{SB2} ^[7]	Automatic power down current – CMOS inputs	$\frac{\overline{CE} \ge V_{CC} - 0.2 \text{ N}}{(\overline{BHE} \text{ and } \overline{BLE}) \ge 0}$ $V_{IN} \ge V_{CC} - 0.2 \text{ N}$ $f = 0, V_{CC} = V_{CC}$	\geq V _{CC} -0.2 V, V or V _{IN} \leq 0.2 V,	_	1	5	-	1	20	μА

Notes

- Notes

 3. V_{IL(min)} = -2.0 V for pulse durations less than 20 ns.

 4. V_{IH(max)} = V_{CC} + 0.75 V for pulse durations less than 20 ns.

 5. Full device AC operation assumes a minimum of 100 μs ramp time from 0 to V_{CC(min)} and 200 μs wait time after V_{CC} stabilization.

 6. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC(typ)}, T_A = 25 °C.

 7. Chip enable (CE) and byte enables (BHE and BLE) need to be tied to CMOS levels to meet the I_{SB1} / I_{SB2} / I_{CCDR} specification. Other inputs can be left floating.



Capacitance

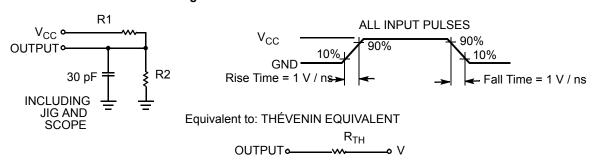
Parameter [8]	Description	Test Conditions	Max	Unit
C _{IN}	Input capacitance	$T_A = 25 ^{\circ}\text{C}, f = 1 \text{MHz}, V_{CC} = V_{CC(typ)}$	10	pF
C _{OUT}	Output capacitance		10	pF

Thermal Resistance

Parameter [8]	Description	Test Conditions	TSOP II	Unit
U/A	Thermal resistance (junction to ambient)	Still air, soldered on a 3 × 4.5 inch, two layer printed circuit board	77	°C/W
$\Theta_{\sf JC}$	Thermal resistance (junction to case)		13	°C/W

AC Test Loads and Waveforms

Figure 2. AC Test Loads and Waveforms



Parameters	2.5 V (2.2 V to 2.7 V)	3.0 V (2.7 V to 3.6 V)	Unit
R1	16667	1103	Ω
R2	15385	1554	Ω
R _{TH}	8000	645	Ω
V_{TH}	1.20	1.75	V

Note

^{8.} Tested initially and after any design or process changes that may affect these parameters.



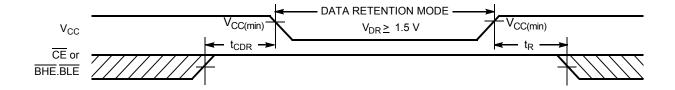
Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions	Min	Typ [9]	Max	Unit	
V_{DR}	V _{CC} for data retention			1.5	_	_	V
I _{CCDR} ^[10]	Data retention current	V_{CC} = 1.5 V, CE \geq V _{CC} - 0.2 V or	Automotive-A	_	_	4	μΑ
		$\frac{\text{CE} \ge \text{V}_{\text{CC}} - 0.2 \text{ V or}}{(\text{BHE and BLE}) \ge \text{V}_{\text{CC}} - 0.2 \text{ V}}$ $\text{V}_{\text{IN}} \ge \text{V}_{\text{CC}} - 0.2 \text{ V or V}_{\text{IN}} \le 0.2 \text{ V}$	Automotive-E	-	_	12	-
t _{CDR} ^[11]	Chip deselect to data retention time			0	_	-	ns
t _R ^[12]	Operation recovery time		CY62137FV30LL-45	45	_	_	ns
			CY62137FV30LL-55	55			

Data Retention Waveform

Figure 3. Data Retention Waveform [13]



- 9. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC(typ)}, T_A = 25 °C

 10. Chip enable (CE) and byte enables (BHE and BLE) need to be tied to CMOS levels to meet the I_{SB1} / I_{SB2} / I_{CCDR} specification. Other inputs can be left floating.

 11. Tested initially and after any design or process changes that may affect these parameters.

 12. Full device operation requires linear V_{CC} ramp from V_{DR} to V_{CC(min)} ≥ 100 μs or stable at V_{CC(min)} ≥ 100 μs.

 13. BHE.BLE is the AND of both BHE and BLE. Deselect the chip by either disabling chip enable signals or by disabling both BHE and BLE.



Switching Characteristics

Parameter [14, 15]	D	45 ns (Aut	omotive-A)	55 ns (Aut	11.24	
Parameter [11, 19]	Description	Min	Max	Min	Max	Unit
Read Cycle		•				•
t _{RC}	Read cycle time	45	_	55	_	ns
t _{AA}	Address to data valid	_	45	_	55	ns
t _{OHA}	Data hold from address change	10	_	10	_	ns
t _{ACE}	CE LOW to data valid	_	45	_	55	ns
t _{DOE}	OE LOW to data valid	-	22	_	25	ns
t _{LZOE}	OE LOW to low Z [16]	5	_	5	_	ns
t _{HZOE}	OE HIGH to high Z [16, 17]	_	18	_	20	ns
t _{LZCE}	CE LOW to low Z [16]	10	_	10	_	ns
t _{HZCE}	CE HIGH to high Z [16, 17]	_	18	_	20	ns
t _{PU}	CE LOW to power-up	0	_	0	_	ns
t _{PD}	CE HIGH to power-down	-	45	_	55	ns
t _{DBE}	BLE/BHE LOW to data valid	_	45	_	55	ns
t _{LZBE}	BLE/BHE LOW to low Z [16, 18]	5	_	10	_	ns
t _{HZBE}	BLE/BHE HIGH to high Z [16, 17]	_	18	_	20	ns
Write Cycle [19]						
t _{WC}	Write cycle time	45	_	55	_	ns
t _{SCE}	CE LOW to write end	35	_	40	_	ns
t _{AW}	Address setup to write end	35	_	40	_	ns
t _{HA}	Address hold from write end	0	_	0	_	ns
t _{SA}	Address setup to write start	0	_	0	_	ns
t _{PWE}	WE pulse width	35	_	40	_	ns
t _{BW}	BLE/BHE LOW to write end	35	_	40	_	ns
t _{SD}	Data setup to write end	25	_	25	-	ns
t _{HD}	Data hold from write end	0	_	0	_	ns
t _{HZWE}	WE LOW to high Z [16, 17]	_	18	-	20	ns
t _{LZWE}	WE HIGH to low Z [16]	10	_	10	_	ns

<sup>Notes
14. Test conditions for all parameters, other than tristate parameters, assume signal transition time of 3 ns (1 V/ns) or less, timing reference levels of V_{CC(typ)}/2, input pulse levels of 0 to V_{CC(typ)}, and output loading of the specified I_{OL} I_{OH} as shown in Figure 2 on page 5.
15. AC timing parameters are subject to byte enable signals (BHE or BLE) not switching when chip is disabled. Please see application note AN13842 for further clarification.
16. At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZDE}, t_{HZDE} is less than t_{LZDE}, and t_{HZWE} is less than t_{LZWE} for any device.
17. t_{HZCE}, t_{HZCE}, t_{HZCE}, t_{HZCE}, t_{HZCE}, tansitions are measured when the outputs enter a high impedance state.
18. If both byte enables are toggled together, this value is 10 ns.
19. The internal write time of the memory is defined by the overlap of WE, CE = V_{|L}, BHE and/or BLE = V_{|L}. All signals are ACTIVE to initiate a write and any of these signals terminate a write by going INACTIVE. The data input setup and hold timing are referenced to the edge of the signal that terminates the write.</sup>



Switching Waveforms

Figure 4. Read Cycle 1: Address Transition Controlled [20, 21]

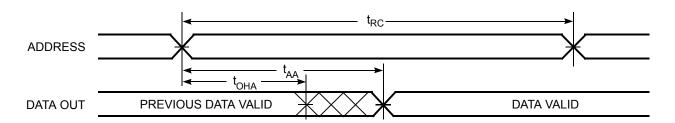
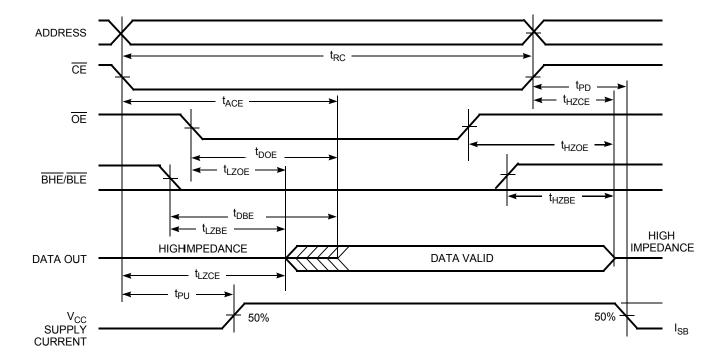


Figure 5. Read Cycle 2: $\overline{\text{OE}}$ Controlled [21, 22]



^{20.} The device is continuously selected. \overline{OE} , $\overline{CE} = V_{\parallel L}$, \overline{BHE} and/or $\overline{BLE} = V_{\parallel L}$. 21. \overline{WE} is HIGH for read cycle.

^{22.} Address valid before or similar to CE and BHE, BLE transition LOW.



Switching Waveforms (continued)

Figure 6. Write Cycle 1: WE Controlled [23, 24, 25]

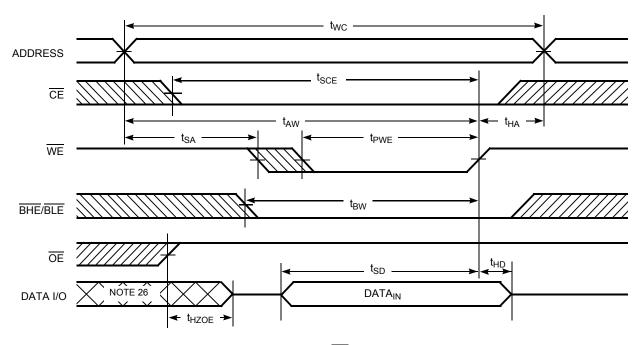
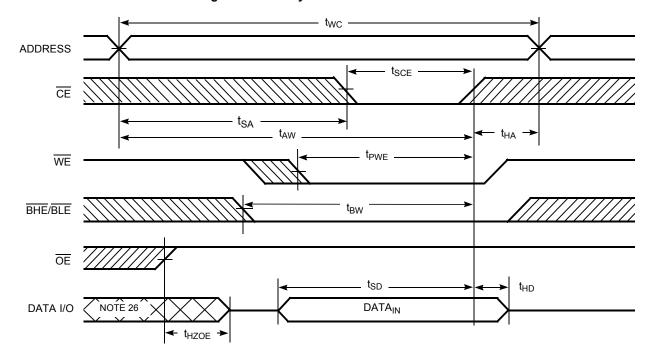


Figure 7. Write Cycle 2: $\overline{\text{CE}}$ Controlled [23, 24, 25]



Notes

- 23. The internal write time of the memory is defined by the overlap of WE, $\overline{CE} = V_{IL}$, \overline{BHE} and/or $\overline{BLE} = V_{IL}$. All signals are ACTIVE to initiate a write and any of these signals terminate a write by going INACTIVE. The data input setup and hold timing are referenced to the edge of the signal that terminates the write.

 24. Data I/O is high impedance if $\overline{OE} = V_{IL}$.

 25. If \overline{CE} goes HIGH simultaneously with $\overline{WE} = V_{IH}$, the output remains in a high impedance state.

 26. During this period, the I/Os are in output state. Do not apply input signals.



Switching Waveforms (continued)

Figure 8. Write Cycle 3: WE Controlled, OE LOW [27]

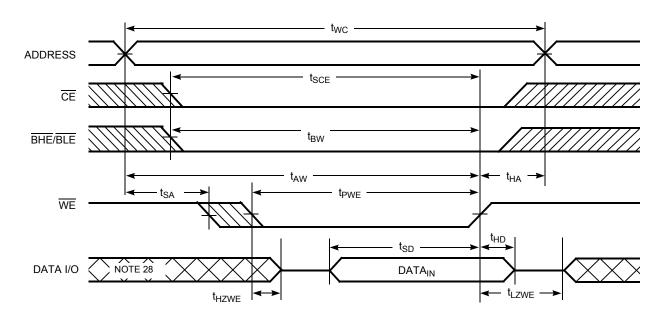
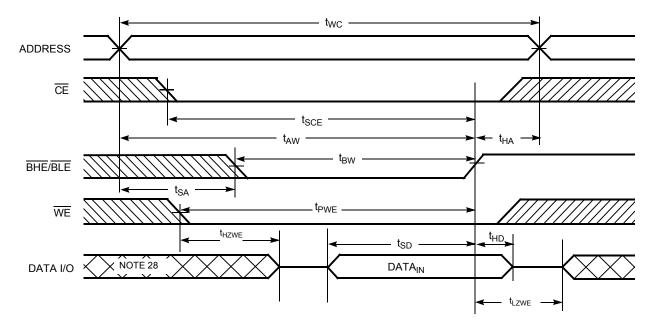


Figure 9. Write Cycle 4: BHE/BLE Controlled, OE LOW [27]



Notes 27. If $\overline{\text{CE}}$ goes HIGH simultaneously with $\overline{\text{WE}}$ = V_{IH}, the output remains in a high impedance state. 28. During this period, the I/Os are in output state. Do not apply input signals.



Truth Table

CE	WE	OE	BHE	BLE	Inputs or Outputs	Mode	Power
Н	Х	Х	X ^[29]	X ^[29]	High Z	Deselect or power-down	Standby (I _{SB})
X ^[29]	Х	Х	Н	Н	High Z	Deselect or power-down	Standby (I _{SB})
L	Н	L	L	L	Data out (I/O ₀ -I/O ₁₅)	Read	Active (I _{CC})
L	Η	L	Н	L	Data out (I/O ₀ –I/O ₇); I/O ₈ –I/O ₁₅ in High Z	Read	Active (I _{CC})
L	Н	L	L	Н	Data out (I/O ₈ –I/O ₁₅); I/O ₀ –I/O ₇ in High Z	Read	Active (I _{CC})
L	Н	Н	L	L	High Z	Output disabled	Active (I _{CC})
L	Н	Н	Н	L	High Z	Output disabled	Active (I _{CC})
L	Η	Ι	L	Н	High Z	Output disabled	Active (I _{CC})
L	L	Χ	L	L	Data in (I/O ₀ –I/O ₁₅)	Write	Active (I _{CC})
L	L	Х	Н	L	Data in (I/O ₀ –I/O ₇); I/O ₈ –I/O ₁₅ in High Z	Write	Active (I _{CC})
L	L	Х	L	Н	Data in (I/O ₈ –I/O ₁₅); I/O ₀ –I/O ₇ in High Z	Write	Active (I _{CC})

Note
29. The 'X' (Don't care) state for the Chip enable (\overline{CE}) and Byte enables (\overline{BHE} and \overline{BLE}) in the truth table refer to the logic state (either HIGH or LOW). Intermediate voltage levels on these pins is not permitted.

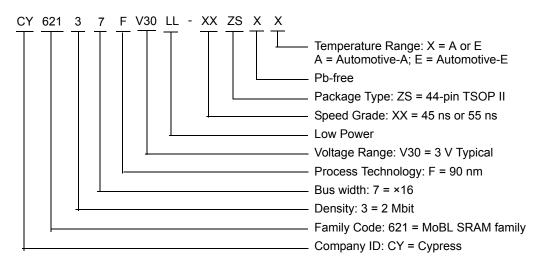


Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62137FV30LL-45ZSXA	51-85087	44-pin TSOP II (Pb-free)	Automotive-A
55	CY62137FV30LL-55ZSXE			Automotive-E

Contact your local Cypress sales representative for availability of these parts.

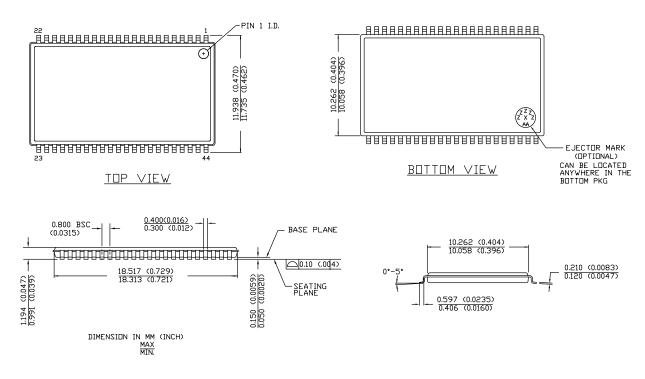
Ordering Code Definitions





Package Diagrams

Figure 10. 44-pin TSOP Z44-II Package Outline, 51-85087



51-85087 *D



Acronyms

Acronym	Description			
BHE	byte high enable			
BLE byte low enable				
CE	chip enable			
CMOS complementary metal oxide semiconduc				
I/O	input/output			
OE	output enable			
SRAM	static random access memory			
TSOP thin small outline package				
WE	write enable			

Document Conventions

Units of Measure

Symbol	Unit of Measure			
°C	degree Celsius			
MHz	megahertz			
μΑ	microampere			
μs	microsecond			
mA	milliampere			
ns	nanosecond			
Ω	ohm			
pF	picofarad			
V	volt			
W	watt			



Document History Page

Document Title: CY62137FV30 MoBL [®] , Automotive 2-Mbit (128 K × 16) Static RAM Document Number: 001-66190						
Rev.	ECN No.	Issue Date	Orig. of Change	Description of Change		
**	3124003	01/12/2011	RAME	Created new Automotive datasheet from document number 001-07141 Rev. *H		
*A	3503362	01/20/2012	TAVA	Updated Functional Description. Updated Package Diagrams. Updated in new template.		



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